

QUERY CONTROL FORM		RTIS USE ONLY	
Application No.	09/ 772, 115	Prepared by	NPB
Examiner-GAU	LOKE - 2811	Date	3/23/04
		No. of queries	1FW
		Tracking Number	05891390
		Week Date	1/19/04

JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

SPECIFICATION	MESSAGE
a. Page Missing	per Notice of Allowability and claim sets (clmpro), claim 27 is allowed, but claim 29 is not shown as allowed in the index of claims.
b. Text Continuity	
c. Holes through Data	
d. Other Missing Text	
e. Illegible Text	
f. Duplicate Text	
g. Brief Description	please advise / renumber the claims, if necessary.
h. Sequence Listing	
i. Appendix	
j. Amendments	
k. Other	
CLAIMS	Thank you
a. Claim(s) Missing	
b. Improper Dependency	
c. Duplicate Numbers	
d. Incorrect Numbering	
e. Index Disagrees	
f. Punctuation	
g. Amendments	
h. Bracketing	initials WAB
i. Missing Text	
j. Duplicate Text	
k. Other	
	initials

Notice of Allowability

Application No.

09/772,115

Examiner

Douglas W Owens

Applicant(s)

LEE ET AL.

Art Unit

2811

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to the amendment filed on November 12, 2003.
 2. ☒ The allowed claim(s) is/are 19, 21 - 25, 27 - 32 and 34 - 39.
 3. ☐ The drawings filed on _____ are accepted by the Examiner.
 4. ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) ☐ All b) ☐ Some* c) ☐ None of the:
 1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).
 - * Certified copies not received: _____.
 5. ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application) since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.
 - (a) ☐ The translation of the foreign language provisional application has been received.
 6. ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121 since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.
- Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. **THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.**
7. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
 8. ☒ CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 - (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) ☐ hereto or 2) ☐ to Paper No. _____.
 - (b) ☒ including changes required by the proposed drawing correction filed 14 February 2002, which has been approved by the Examiner.
 - (c) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No. _____.

Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the margin according to 37 CFR 1.121(d).

9. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

- | | |
|--|--|
| 1 <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 5 <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 2 <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 6 <input type="checkbox"/> Interview Summary (PTO-413), Paper No. _____ |
| 3 <input type="checkbox"/> Information Disclosure Statements (PTO-1449 or PTO/SB/08), Paper No. _____ | 7 <input checked="" type="checkbox"/> Examiner's Amendment/Comment |
| 4 <input type="checkbox"/> Examiner's Comment Regarding Requirement for Deposit of Biological Material | 8 <input type="checkbox"/> Examiner's Statement of Reasons for Allowance |
| | 9 <input type="checkbox"/> Other |

26. (canceled) The semiconductor structure of Claim 19, wherein the silicide strap comprises a refractory metal layer reacted with semiconductor material in the conductive element, the dielectric spacer and the semiconductor substrate.

27. (presently amended) The semiconductor structure of Claim 26,¹⁹ wherein the refractory metal layer directly contacts semiconductor material comprising amorphous silicon in the conductive element, the dielectric spacer and the semiconductor substrate.

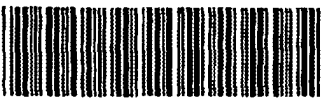
28. (previously added) The semiconductor structure of Claim 19,² wherein the conductive element is a gate electrode.

29. (previously added) The semiconductor structure of Claim 28,³ further comprising a gate dielectric layer located between the semiconductor substrate and the gate electrode.

30. (previously added) The semiconductor structure of Claim 19,⁴ further comprising a source/drain region located in the semiconductor substrate, wherein the refractory metal layer silicide strap contacts the source/drain region.

31. (previously added) The semiconductor structure of Claim 19,⁵ wherein the dielectric spacer comprises silicon oxide or silicon nitride.

32. (presently amended) The semiconductor structure of Claim 19,⁶ wherein the refractory metal layer silicide strap comprises cobalt silicide.

Issue Classification 	Application No.	Applicant(s)	
	09/772,115	LEE ET AL.	
	Examiner	Art Unit	
	Douglas W Owens	2811	

ISSUE CLASSIFICATION										
ORIGINAL				CROSS REFERENCE(S)						
CLASS	SUBCLASS			CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)					
257	383			257	382	384				
INTERNATIONAL CLASSIFICATION										
H	0	1	L							
				29/94						
				/						
				/						
				/						
				/						

Douglas W. Owens 12/4/03 (Assistant Examiner) (Date)		Total Claims Allowed: 17	
[Signature] 12/4/03 (Legal Instruments Examiner) (Date)		[Signature] 12/6/03 (Primary Examiner) (Date)	
		O.G. Print Claim(s) 19	O.G. Print Fig. 2G

<input type="checkbox"/> Claims renumbered in the same order as presented by applicant						<input type="checkbox"/> CPA		<input type="checkbox"/> T.D.		<input type="checkbox"/> R.1.47	
Final	Original		Final	Original		Final	Original		Final	Original	
	1		5	31			61			121	
	2		6	32			62			122	
	3			33			63			123	
	4		12	34			64			124	
	5		13	35			65			125	
	6		14	36			66			126	
	7		15	37			67			127	
	8		16	38			68			128	
	9		17	39			69			129	
	10			40			70			130	
	11			41			71			131	
	12			42			72			132	
	13			43			73			133	
	14			44			74			134	
	15			45			75			135	
	16			46			76			136	
	17			47			77			137	
	18			48			78			138	
1	19			49			79			139	
	20			50			80			140	
7	21			51			81			141	
8	22			52			82			142	
9	23			53			83			143	
10	24			54			84			144	
11	25			55			85			145	
	26			56			86			146	
	27			57			87			147	
2	28			58			88			148	
3	29			59			89			149	
4	30			60			90			150	